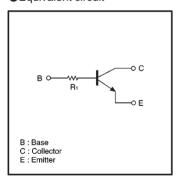
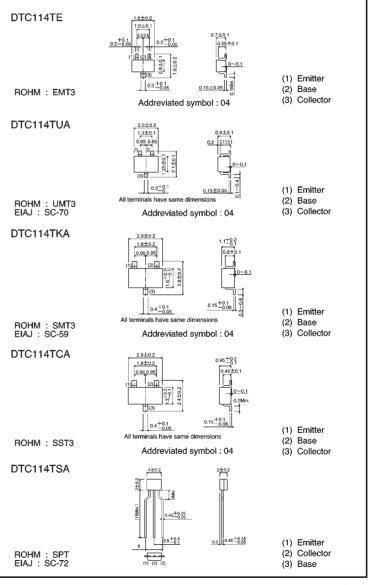
Digital transistors (built in resistor) DTC114TE / DTC114TUA / DTC114TKA DTC114TCA / DTC114TSA

Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thinfilm resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.
- StructureNPN digital transistor(With single built in resistor)
- ■Equivalent circuit



External dimensions (Units: mm)



(96-311-C114T)

●Absolute maximum ratings (Ta = 25°C)

| Parameter | Symbol | | Unit | | | | |
|-----------------------------|--------|-----|------|-----|----|-----|-------|
| | | Е | UA | KA | CA | SA | Offic |
| Collector-base voltage | Vсво | | V | | | | |
| Collector-emitter voltage | Vceo | | V | | | | |
| Emitter-base voltage | VEBO | | V | | | | |
| Collector current | lc | | mA | | | | |
| Collector power dissipation | Pc | 150 | | 200 | | 300 | mW |
| Junction temperature | Tj | | °C | | | | |
| Storage temperature | Tstg | | Ĉ | | | | |

●Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|--------------------------------------|-----------------------|------|------|------|------|------------------------------|
| Collector-base breakdown voltage | ВУсво | 50 | _ | _ | ٧ | Ic=50 μ A |
| Collector-emitter breakdown voltage | BVCEO | 50 | _ | _ | ٧ | lc=1mA |
| Emitter-base breakdown voltage | BVEBQ | 5 | _ | _ | ٧ | IE=50 μ A |
| Collector cutoff current | Ісво | _ | _ | 0.5 | μА | V _{CB} =50V |
| Emitter cutoff current | Ієво | _ | _ | 0.5 | μA | V _{EB} =4V |
| Collector-emitter saturation voltage | V _{CE} (sat) | _ | _ | 0.3 | ٧ | Ic/I _B =10mA/1mA |
| DC current transfer ratio | hfE | 100 | 300 | 600 | _ | VcE=5V, Ic=1mA |
| Input resistance | R ₁ | 7 | 10 | 13 | kΩ | _ |
| Transition frequency | fτ | _ | 250 | | MHz | VcE=10V, IE=-5mA, f=100MHz * |

^{*} Transition frequency of the device

Packaging specifications

| | Package | EMT3 | UMT3 | SMT3 | SST3 | SPT |
|-----------|------------------------------|--------|--------|--------|--------|--------|
| | Packaging type | Taping | Taping | Taping | Taping | Taping |
| | Code | TL | T106 | T146 | T116 | TP |
| Part No. | Basic ordering unit (pieces) | 3000 | 3000 | 3000 | 3000 | 5000 |
| DTC114TE | | 0 | _ | _ | _ | _ |
| DTC114TU | 4 | _ | 0 | _ | _ | _ |
| DTC114TKA | ١ | _ | _ | 0 | _ | _ |
| | | | | _ | l | |
| DTC114TCA | 4 | _ | _ | _ | 0 | _ |

Electrical characteristic curves

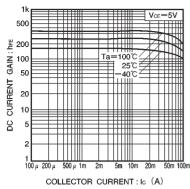


Fig.1 DC current gain vs. collector current

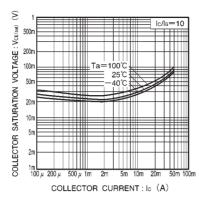


Fig.2 Collector-emitter saturation voltage vs. collector current